



SB2060LCT

DUAL LOW VF SCHOTTKY RECTIFIER

VOLTAGE 60 Volts **CURRENT** 20 Amperes

FEATURES

- Low forward voltage drop, low power losses
- High efficiency operation
- In compliance with EU RoHS 2002/95/EC directives

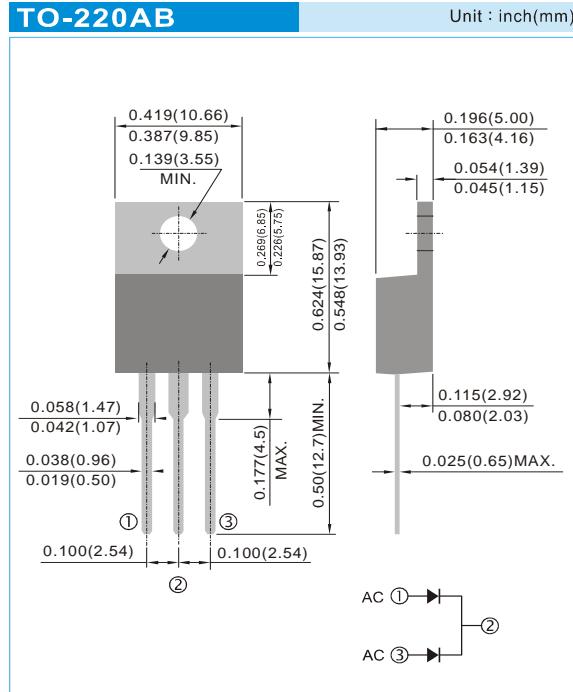
MECHANICAL DATA

Case : TO-220AB, Plastic

Terminals : Solderable per MIL-STD-750, Method 2026

Weight: 0.0655 ounces, 1.859 grams

TO-220AB



MAXIMUM RATINGS(T_A=25°C unless otherwise noted)

PARAMETER	SYMBOL	VALUE	UNIT
Maximum repetitive peak reverse voltage	V _{RRM}	60	V
Maximum average forward rectified current (Fig.4)	I _{F(AV)} per device per diode	20 10	A
Peak forward surge current 8.3ms single half sine-wave superimposed on rated load per diode	I _{FSM} per diode	145	A
Typical thermal resistance	R _{θJC}	2.5	°C / W
Operating junction	T _J	-55 to + 125	°C
Storage temperature range	T _{STG}	-55 to + 150	°C

ELECTRICAL CHARACTERISTICS(T_A=25°C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Breakdown voltage	V _{BR}	I _R =1mA	64	68	-	V
Instantaneous forward voltage per diode ⁽¹⁾	V _F	I _F =5A I _F =10A T _J =25°C	-	0.44 0.51	0.51 0.60	V
		I _F =5A I _F =10A T _J =125°C	-	-	0.44 0.56	V
Reverse current per diode ⁽²⁾	I _R	V _R =60V T _J =25°C T _J =100°C	-	-	0.5 20	mA

Note.1.Pulse test : 380μs pulse width, 1% duty cycle

2.Pulse test : Pulse width ≤ 2.5ms



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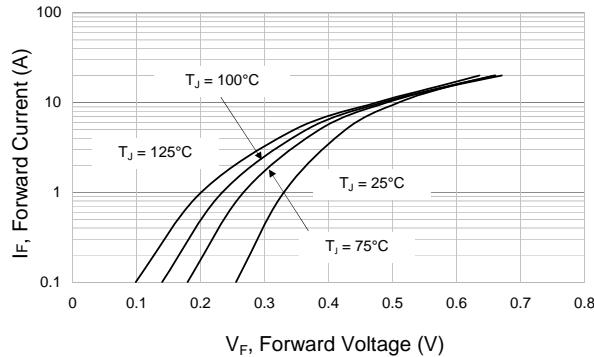


Fig.1 Typical Forward Characteristics Per Diode

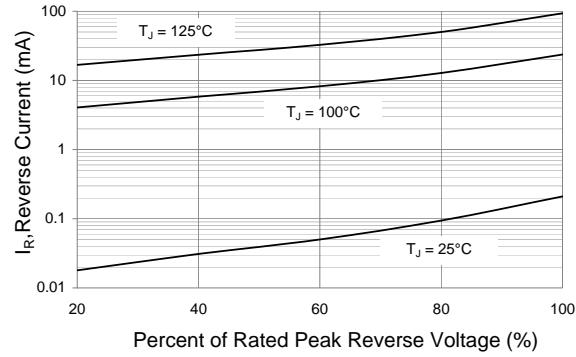


Fig.2 Typical Reverse Characteristics Per Diode

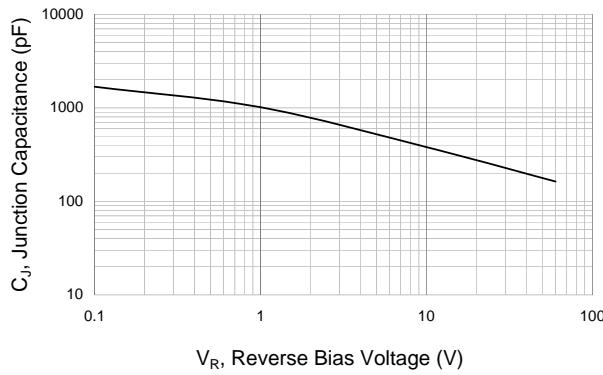


Fig.3 Typical Junction Capacitance Per Diode

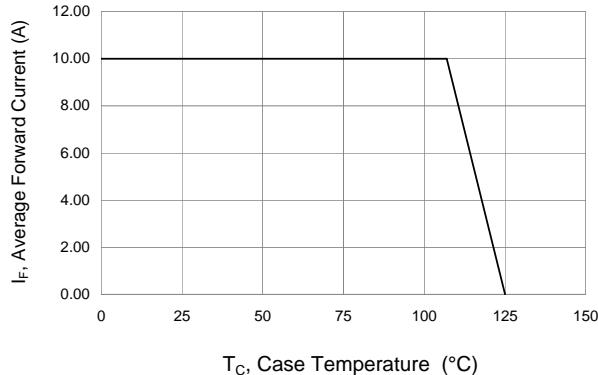


Fig.4 Forward Current Derating Curve Per Diode

单击下面可查看定价，库存，交付和生命周期等信息

[>>Panjit\(强茂\)](#)